

26NM60Z-U3

Power MOSFET

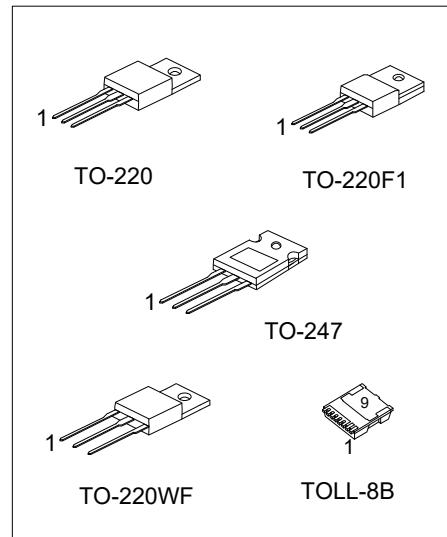
26A, 600V N-CHANNEL SUPER-JUNCTION
MOSFET

■ DESCRIPTION

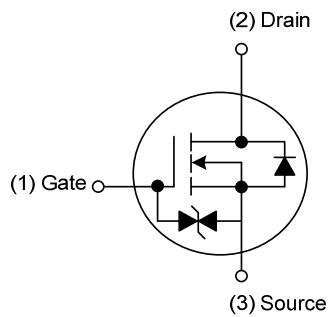
The **UTC 26NM60Z-U3** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at AC-DC converters for power applications.

■ FEATURES

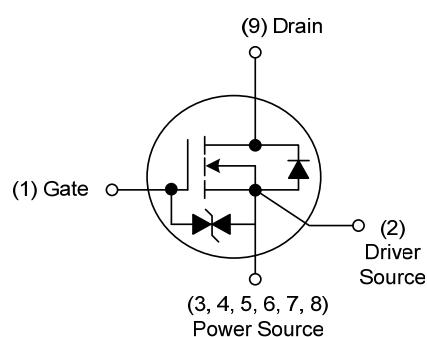
- * $R_{DS(ON)} \leq 0.15 \Omega$ @ $V_{GS}=10V$, $I_D=6.5A$
- * Fast switching capability
- * Avalanche energy tested
- * Improved dv/dt capability, high ruggedness
- * With ESD Protected: HBM=2KV



■ SYMBOL



TO-220 / TO-220F1
TO-220WF / TO-247

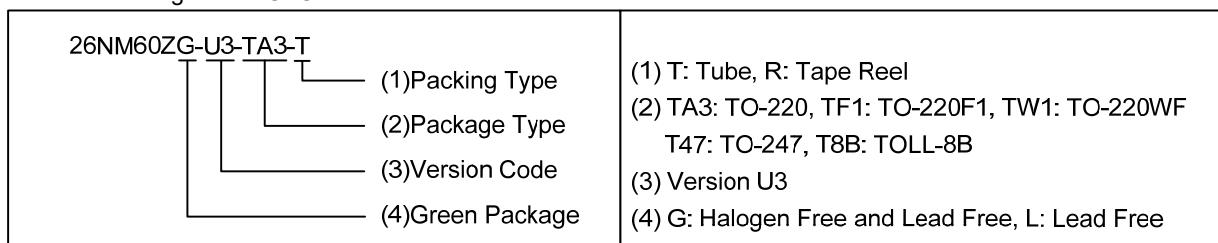


TOLL-8B

■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment									Packing
Lead Free	Halogen Free		1	2	3	4	5	6	7	8	9	
26NM60ZL-U3-TA3-T	26NM60ZG-U3-TA3-T	TO-220	G	D	S	-	-	-	-	-	-	Tube
26NM60ZL-U3-TF1-T	26NM60ZG-U3-TF1-T	TO-220F1	G	D	S	-	-	-	-	-	-	Tube
26NM60ZL-U3-TW1-T	26NM60ZG-U3-TW1-T	TO-220WF	G	D	S	-	-	-	-	-	-	Tube
26NM60ZL-U3-T47-T	26NM60ZG-U3-T47-T	TO-247	G	D	S	-	-	-	-	-	-	Tube
26NM60ZL-U3-T8B-R	26NM60ZG-U3-T8B-R	TOLL-8B	G	S	S	S	S	S	S	S	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source



■ MARKING

TO-220 / TO-220F1 / TO-220WF / TO-247	TOLL-8B
<p>Version Code Lot Code 1 L: Lead Free G: Halogen Free Date Code</p>	<p>Version Code Lot Code 1 L: Lead Free G: Halogen Free Date Code</p>

■ ABSOLUTE MAXIMUM RATINGS ($T_c=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	Continuous	I_D	26	A
	Pulsed (Note 2)	I_{DM}	78	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	62.5	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	1.2	V/ns
Power Dissipation	TO-220	P_D	115	W
	TO-220F1/TO-220WF		33	W
	TO-247		130	W
	TOLL-8B		200	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 10\text{mH}$, $I_{AS} = 3.5\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$ Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 26\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220 / TO-220F1	θ_{JA}	62.5	$^\circ\text{C/W}$
	TO-220WF		40	$^\circ\text{C/W}$
	TO-247		35 (Note)	$^\circ\text{C/W}$
	TOLL-8B			
Junction to Case	TO-220	θ_{JC}	1.08	$^\circ\text{C/W}$
	TO-220F1/TO-220WF		3.79	$^\circ\text{C/W}$
	TO-247		0.96	$^\circ\text{C/W}$
	TOLL-8B		0.625 (Note)	$^\circ\text{C/W}$

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

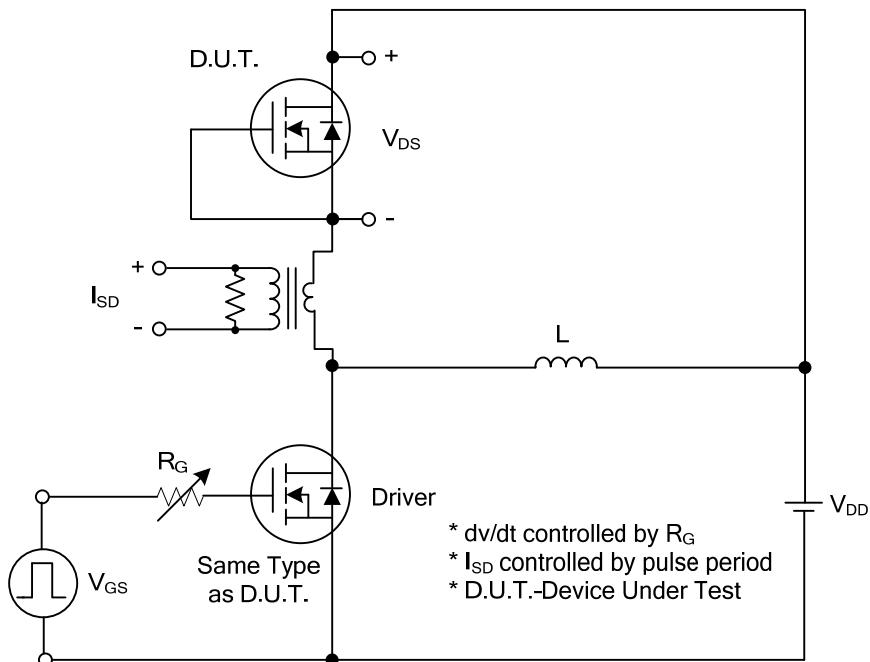
■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	600			V
Drain-Source Leakage Current	I_{DSS}	$V_{\text{DS}}=600\text{V}, V_{\text{GS}}=0\text{V}$		1		μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$			± 10	μA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{\text{GS}(\text{TH})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	3.0		4.5	V
Static Drain-Source On-State Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=6.5\text{A}$			0.15	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{\text{GS}}=0\text{V}, V_{\text{DS}}=50\text{V}, f=1\text{MHz}$		1400		pF
Output Capacitance	C_{OSS}			400		pF
Reverse Transfer Capacitance	C_{RSS}			14		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge (Note 1)	Q_G	$V_{\text{DS}}=480\text{V}, V_{\text{GS}}=10\text{V}, I_{\text{D}}=13\text{A}$ (Note 1, 2)		52		nC
Gate-Source Charge	Q_{GS}			11		nC
Gate-Drain Charge	Q_{DD}			27		nC
Turn-On Delay Time (Note 1)	$t_{\text{D}(\text{ON})}$	$V_{\text{DD}}=100\text{V}, V_{\text{GS}}=10\text{V}, I_{\text{D}}=13\text{A}$ $R_{\text{G}}=25\Omega$ (Note 1, 2)		21		ns
Turn-On Rise Time	t_{R}			37		ns
Turn-Off Delay Time	$t_{\text{D}(\text{OFF})}$			181		ns
Turn-Off Fall Time	t_{F}			77		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I_{S}				26	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				78	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	$I_{\text{S}}=26\text{A}, V_{\text{GS}}=0\text{V}$			1.4	V
Body Diode Reverse Recovery Time (Note 1)	t_{rr}	$I_{\text{S}}=26\text{A}, V_{\text{GS}}=0\text{V},$ $dI_{\text{F}}/dt=100\text{A}/\mu\text{s}$		404		nS
Body Diode Reverse Recovery Charge	Q_{rr}			6155		nC

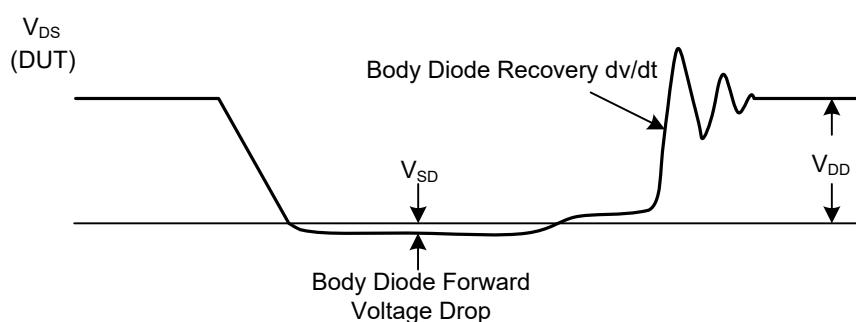
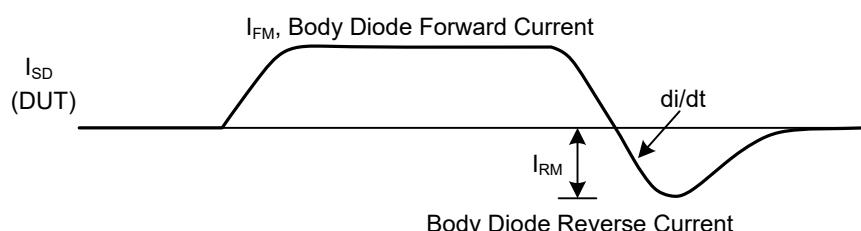
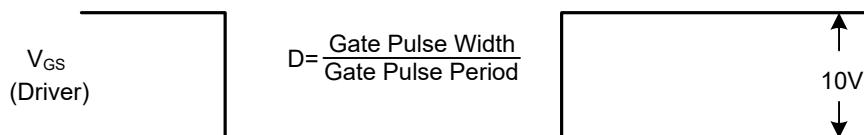
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

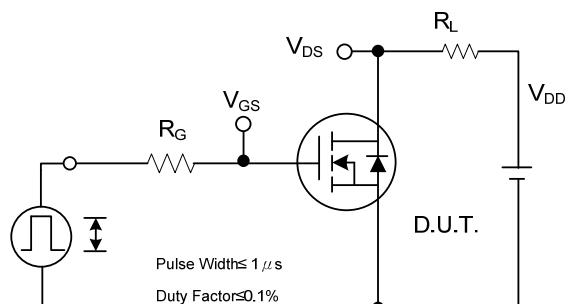


Peak Diode Recovery dv/dt Test Circuit

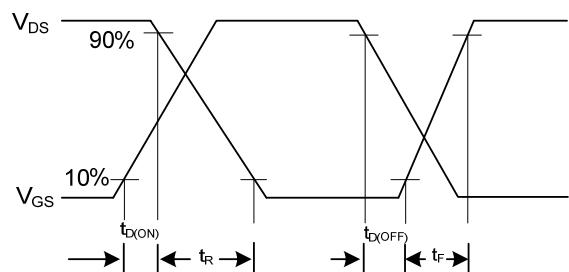


Peak Diode Recovery dv/dt Waveforms

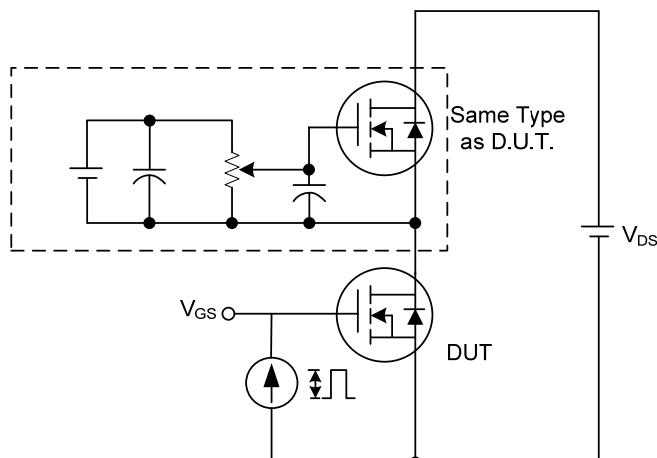
■ TEST CIRCUITS AND WAVEFORMS



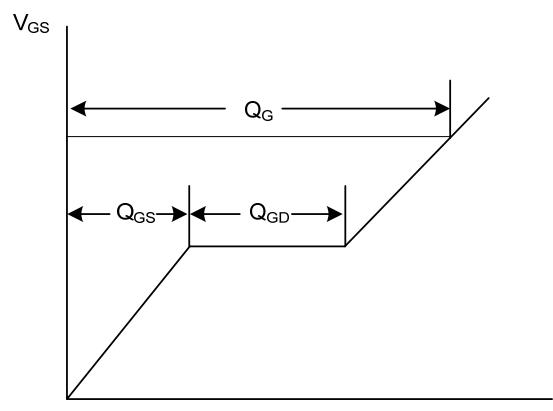
Switching Test Circuit



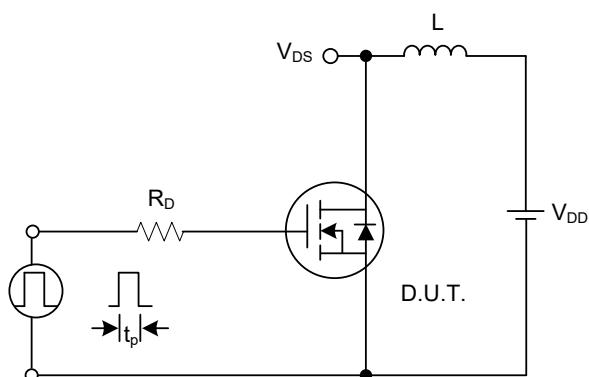
Switching Waveforms



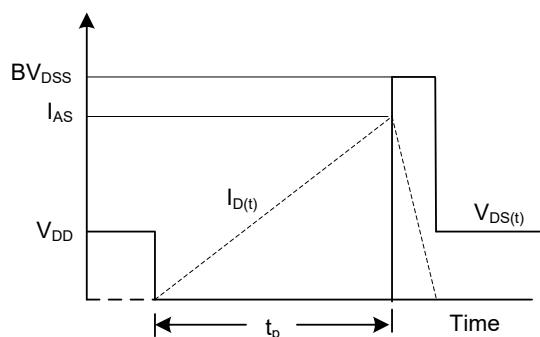
Gate Charge Test Circuit



Gate Charge Waveform

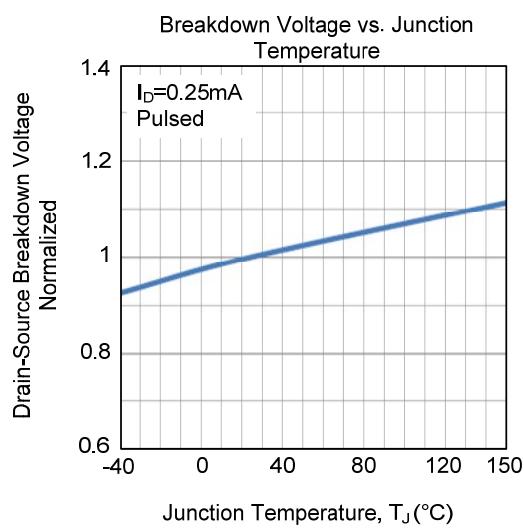
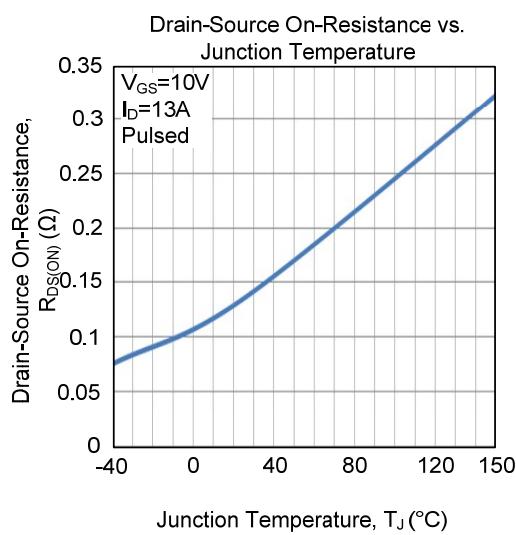
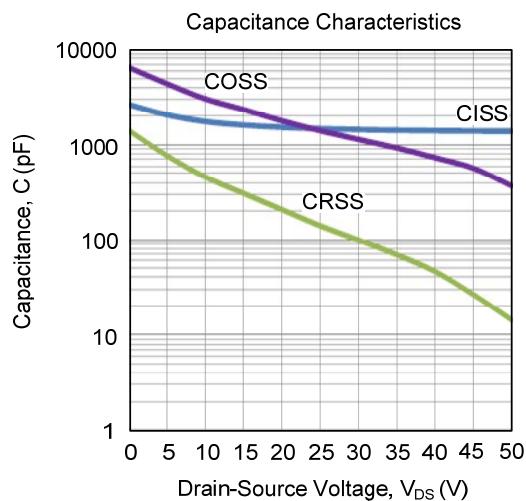
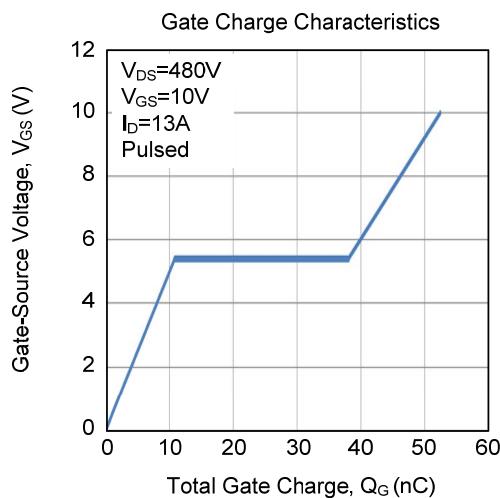
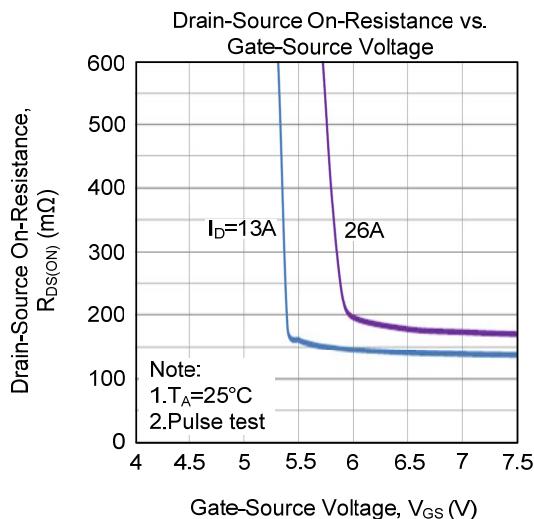
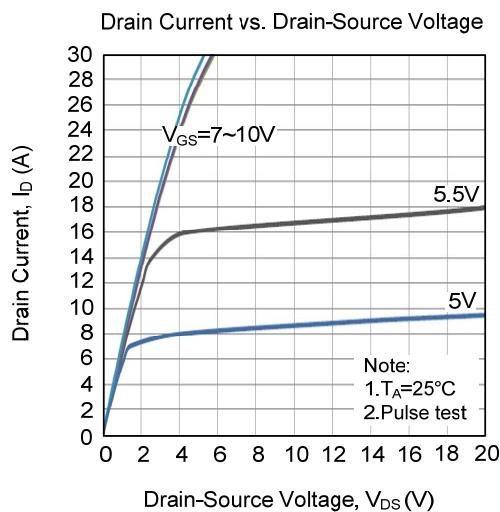


Unclamped Inductive Switching Test Circuit

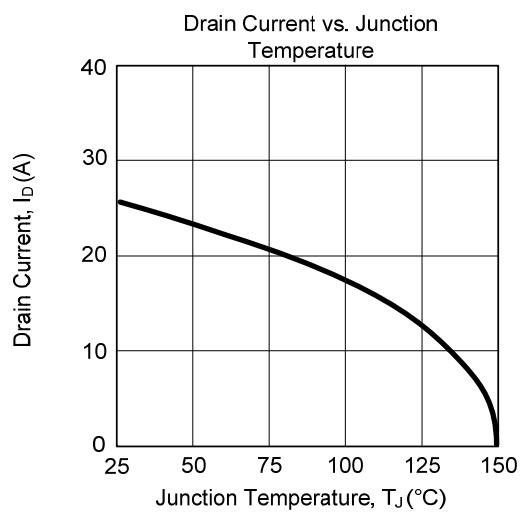
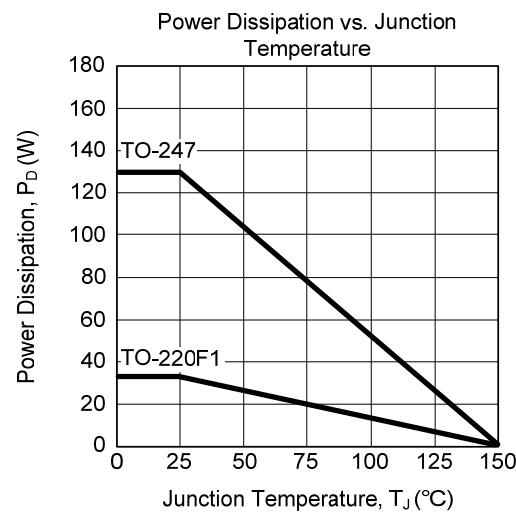
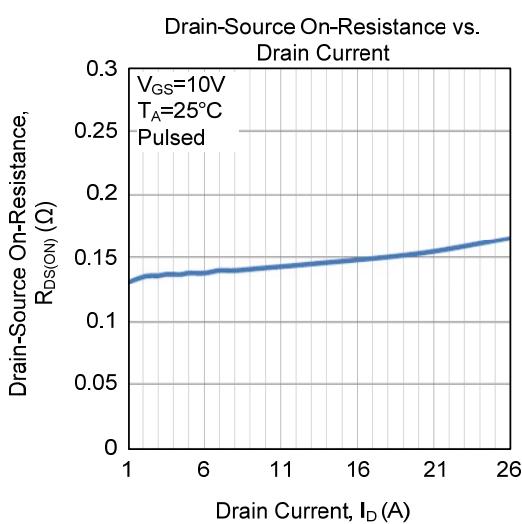
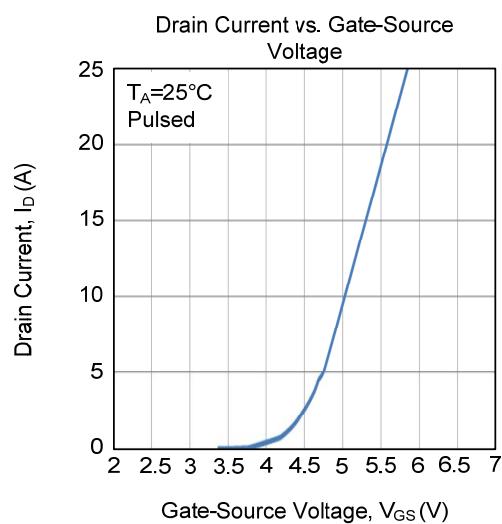
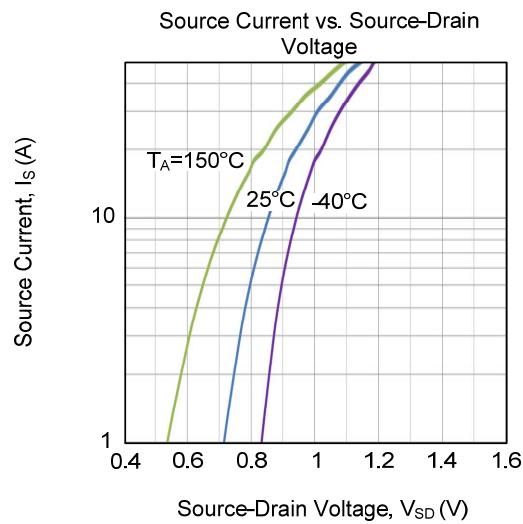
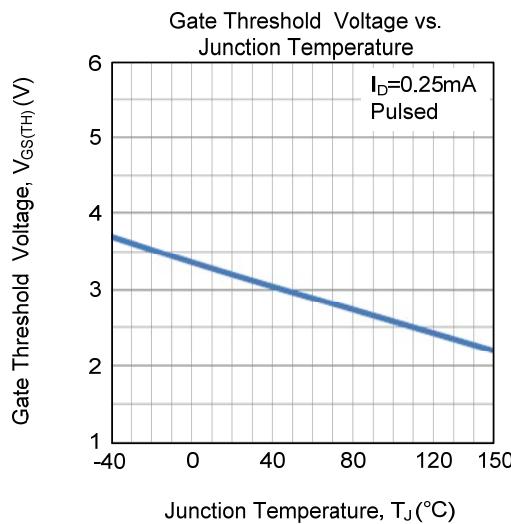


Unclamped Inductive Switching Waveforms

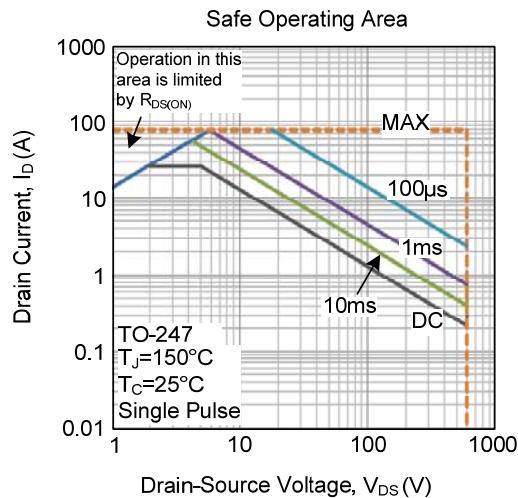
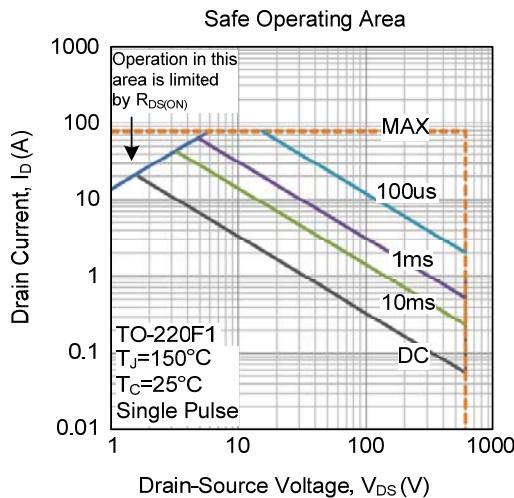
■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



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